



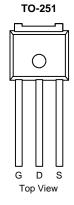
N-Channel 60 V (D-S) MOSFET

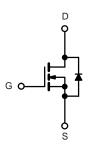
PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$ $I_D(A)$		
60	0.0093 at V _{GS} = 10 V	55	
	0.0122 at V _{GS} = 4.5 V	50	

FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET
- Material categorization:







N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	,	55		
	T _C = 100 °C	l l _D	50 ^a		
Pulsed Drain Current		I _{DM}	165	А	
Continuous Source Current (Diode Conduction)		I _S	50 ^a		
Avalanche Current		I _{AS}	50	1	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Mayimum Dayor Dissination	T _C = 25 °C	В	136	W	
Maximum Power Dissipation	T _A = 25 °C	P _D	3 ^b , 8.3 ^{b, c}]	
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian de Ambienta	t ≤ 10 sec	R _{thJA}	15	18	
Maximum Junction-to-Ambient ^a	Steady State	'`thJA	40	50	°C/W
Maximum Junction-to-Case		R _{thJC}	0.85	1.1	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$



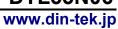


SPECIFICATIONS ($T_J = 25$	°C, unless o	otherwise noted)					
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static	•		•				
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	\ \ \	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		V _{GS} = 10 V, I _D = 20 A		0.0074	0.0093	Ω	
	В	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0160		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.0200		
		$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$			0.0122		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic				•			
Input Capacitance	C _{iss}			2650		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		470			
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Q_g			47	70	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10			
Gate-Drain Charge ^c	Q_{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V, } R_L = 0.6 \Omega$ $I_D \cong 50 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 2.5 \Omega$		15	25	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				165	Α	
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		45	100	ns	

Notes:

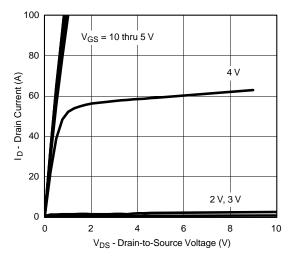
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

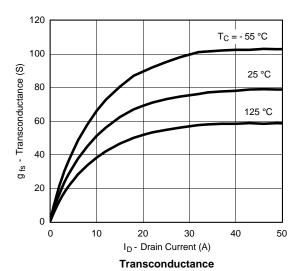




TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics



4000 3500 3000 C_{iss} C - Capacitance (pF) 2500 2000 1500 1000 $\mathsf{C}_{\mathsf{oss}}$ 500 $\mathsf{C}_{\mathsf{rss}}$ 0 0 10 20 30 50 60

V_{DS} - Drain-to-Source Voltage (V)

Capacitance

100
80
(V) treating 40

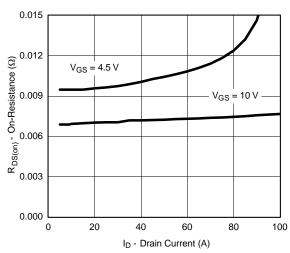
Tc = 125 °C

25 °C

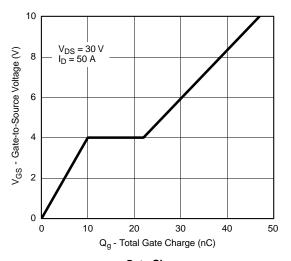
-55 °C

VGS - Gate-to-Source Voltage (V)

Transfer Characteristics



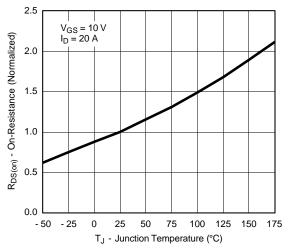
On-Resistance vs. Drain Current



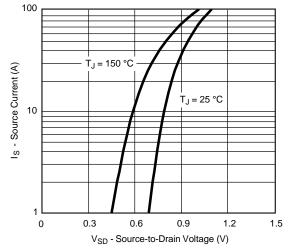
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



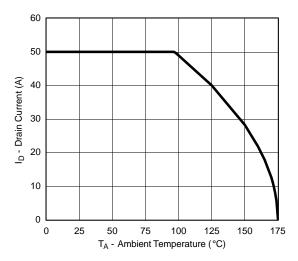
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

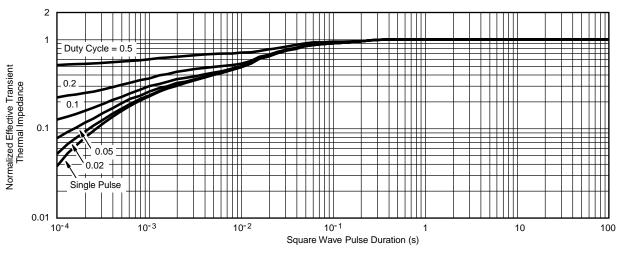


THERMAL RATINGS



1000 Limited by R_{DS(on)}* 100 10 µs 100 µs I_D - Drain Current (A) 10 1 ms 10 ms 100 ms DC T_C = 25 °C Single Pulse 0.1 0.01 L 0.1 100 $\label{eq:VDS} V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ ^*V_{GS} \text{ > minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$ Safe Operating Area

Maximum Drain Current vs. Ambient Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

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